

# RJK2009DPM

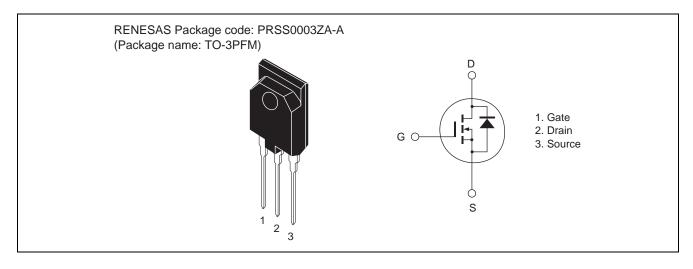
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G0474-0300 Rev.3.00 Jun 30, 2010

#### **Features**

- Low on-resistance
- Low leakage current
- High speed switching

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	200	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	40	А
Drain peak current	I <sub>D (pulse)</sub> Note1	160	Α
Body-drain diode reverse drain current	I <sub>DR</sub>	40	Α
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	160	Α
Avalanche current	I <sub>AP</sub> Note3	40	Α
Avalanche energy	E <sub>AR</sub> Note3	106	mJ
Channel dissipation	Pch Note2	60	W
Channel to case thermal impedance	θch-c	2.08	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

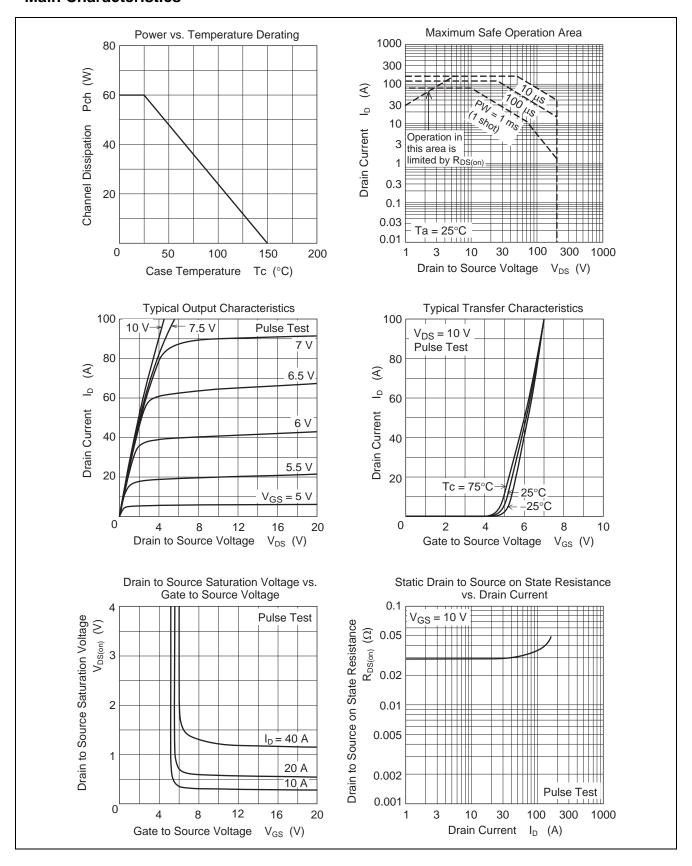
# **Electrical Characteristics**

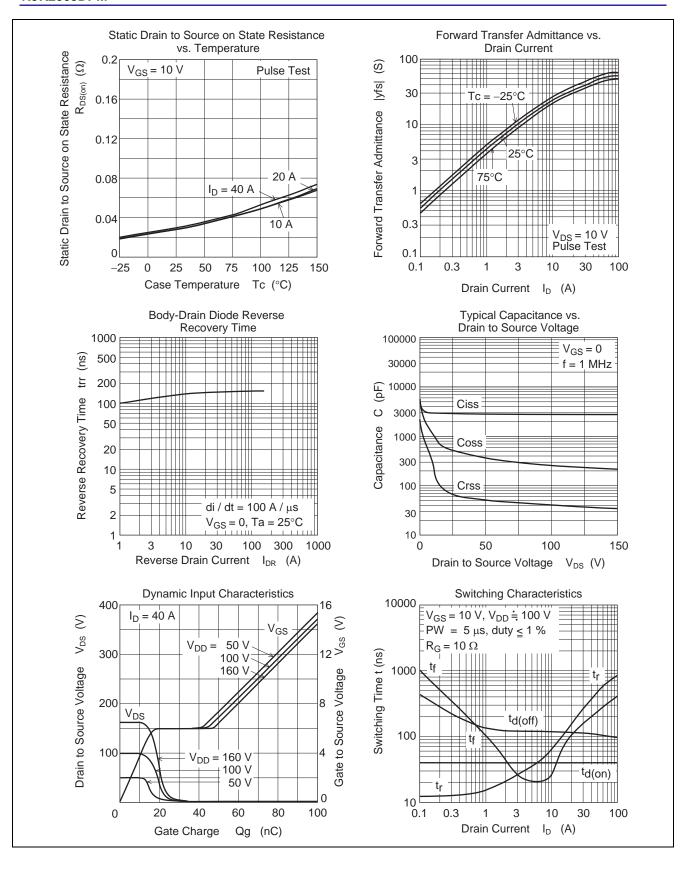
 $(Ta = 25^{\circ}C)$ 

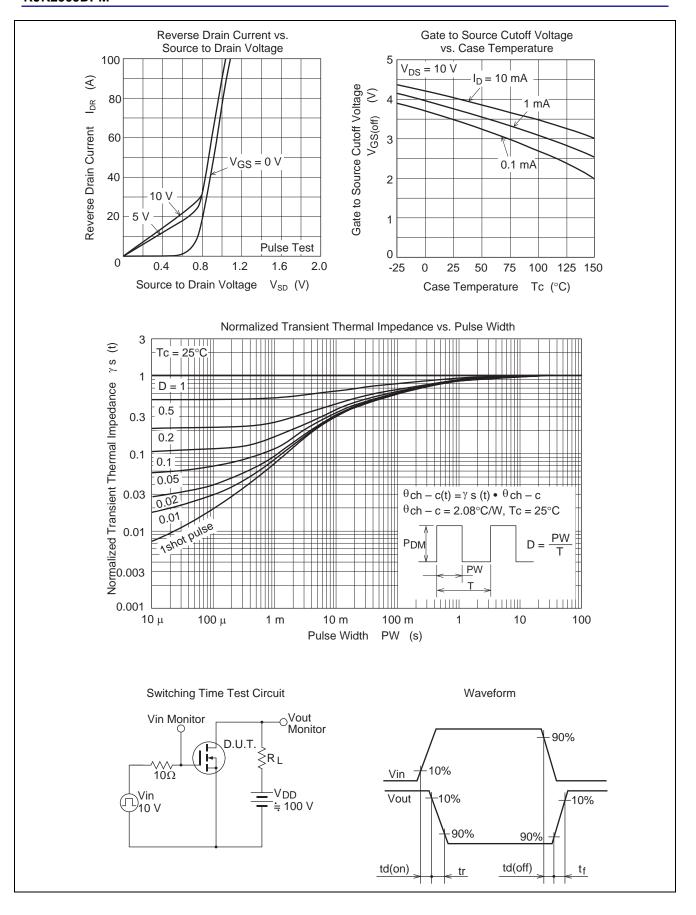
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200		_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	y <sub>fs</sub>	20	33	_	S	$I_D = 20 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Static drain to source on state	R <sub>DS(on)</sub>	_	0.029	0.036	Ω	$I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance						
Input capacitance	Ciss	_	2900	_	pF	$V_{DS} = 25 \text{ V}, V_{GS} = 0,$ f = 1  MHz
Output capacitance	Coss	_	520	_	pF	
Reverse transfer capacitance	Crss	_	66	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	40	_	ns	$I_D = 20 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t <sub>r</sub>	_	160	_	ns	$R_L = 5 \Omega$ , $Rg = 10 \Omega$
Turn-off delay time	$t_{d(off)}$	_	120	_	ns	
Fall time	t <sub>f</sub>	_	110	_	ns	
Total gate charge	Qg	_	72	_	nC	$V_{DD} = 160 \text{ V}, V_{GS} = 10 \text{ V},$
Gate to source charge	Qgs	_	16	_	nC	I <sub>D</sub> = 40 A
Gate to drain charge	Qgd	_	31	_	nC	
Body-drain diode forward voltage	$V_{DF}$	_	0.9	1.4	V	$I_F = 40 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	150	_	ns	$I_F = 40 \text{ A}, V_{GS} = 0,$
Body-drain diode reverse recovery charge	Q <sub>rr</sub>	_	0.8	_	μС	diF/dt = 100 A/μs

Notes: 4. Pulse test

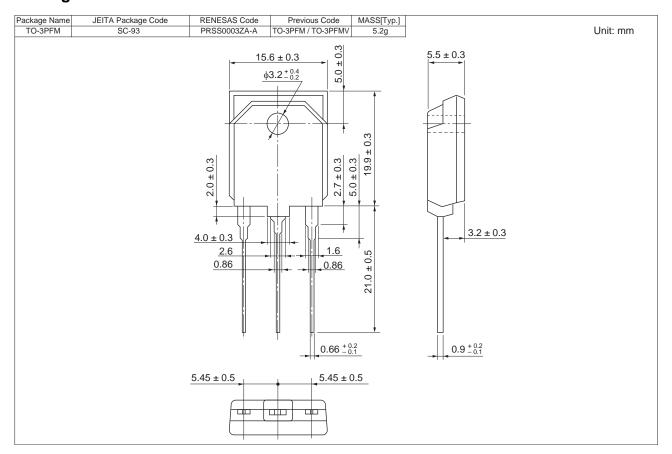
#### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part Name	Quantity	Shipping Container
RJK2009DPM-E	30 pcs	Plastic magazine

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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